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Sheet	1	of	1
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Application / Conf. No.	10/693,468 / 2533
Filing Date	October 24, 2003
First Named Inventor	Kevin T. Look
Art Unit	<del>2810</del> 2827
Examiner Name	Viet Q. Nguyen
Attorney Docket Number	X-719-ID-2D US

Examiner Initials *	Cite No.¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code (if known)			
W B B B B B B B B B		US- 4,661,833	04-28-87	Mizutani	
		US- 5,650,649	07-22-97	Tsukiji	
		US- 5,708,291	01-13-98	Bohr et al.	
		US- 5,851,891	12-22-98	Dawson et al.	
		US- 5,885,874	03-23-99	Gardner	
		US- 5,960,285	09-28-99	Hong	
		US- 6,140,688	10-31-00	Gardner et al.	
		US- 6,268,622	07-31-01	Shone et al.	
		US- 6,525,397	02-25-03	Kalnitsky et al.	
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**VIET Q. NGUYEN**  
**PRIMARY EXAMINER**

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**Examiner  
Signature**

V. Nguyen

Date Considered

3/20/05

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Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application / Conf. No.	<del>Unknown</del> 101 693,468
		Filing Date	October 24, 2003
		First Named Inventor	Kevin T. Look
		Art Unit	<del>Unknown</del> 2827
		Examiner Name	<del>Unknown</del> V. Nguyen
Sheet 1 of 2	Attorney Docket Number	X-719-ID-2D US	

U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No.¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code (if known)				
W		US-	5,627,400	05-06-92	Koga	
W		US-	5,656,528	08-12-97	Wahlstrom	
W		US-	5,821,160	10-13-98	Rodriguez et al.	
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PRIMARY EXAMINER

FOREIGN PATENT DOCUMENTS						
Examiner Initials *	Cite No. *	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code *	Number - Kind Code * (if known)			
W		JP	40623289 A	08-01-94	Kou	
W		JP	360009160 A	01-18-85	Fukumoto et al.	
W		JP	408264660 A	10-11-96	Yamamoto	
W		JP	2000077356 A	03-14-00	Sheen	
W		JP	406232389 A	08-19-94	Kou	
W		JP	363079377 A	04-09-88	Kita	
W		JP	406163906 A	06-10-94	Natsume	

Examiner Signature	V. Nguyen	Date Considered	3/29/05
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Sheet	2	of	2	Attorney Docket Number	X-719-1D-2D US

OTHER - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T *
W		"Boron Diffusion And Penetration In Ultrathin Oxide With Poly-Si Gate"; Cao et al.; IEEE Electron Device Letters; Vol. 19; No. 8; August 1998; pp. 291-293	
W		"Flat-band Voltage Shifts In P-MOS Devices Caused By Carrier Activation In P+-Polycrystalline Silicon and Boron Penetration"; Aoyama et al.; 1997 IEEE; pp. 26.1.1 - 26.1.4	
W		"A PROM Element Based On Salicide Agglomeration Of Poly Fuses In A CMOS Logic Process"; Alavi et al.; 1997 IEEE; pp. 34.3.1 - 34.3.4	
W		"Effects Of Thermal Processes After Silicidation On The Performance Of TiSi <sub>2</sub> /Polysilicon Gate Device"; Jang et al.; IEEE Transactions On Electron Devices; Vol. 46; No. 12; December 1999; pp. 2353-2356	
W		"Comparison Of Transformation To Low-Resistivity Phase And Agglomeration Of TiSi <sub>2</sub> and CoSi <sub>2</sub> "; Lasky et al.; IEEE Transaction On Electron Devices; Vol. 38; No. 2; February 1991; pp. 262-269	
W		"CoSi <sub>2</sub> Integrated Fuses On Poly Silicon For Low Voltage 0.18 um CMOS Application"; Kalnitsky et al.; 1999 IEEE; 4 pages	

VIET Q. NGUYEN  
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Examiner Signature	V. Nguyen	Date Considered	3/20/05
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